

FEATURES

- 10 years minimum data retention in the absence of external power
- Data is automatically protected during power loss
- Directly replaces 8k x 8 volatile static RAM or EEPROM
- Unlimited write cycles
- Low-power CMOS
- JEDEC standard 28-pin DIP package
- Read and write access times as fast as 70 ns
- Lithium energy source is electrically disconnected to retain freshness until power is applied for the first time
- Full $\pm 10\%$ V_{CC} operating range (DS1225AD)
- Optional $\pm 5\%$ V_{CC} operating range (DS1225AB)
- Optional industrial temperature range of -40°C to $+85^{\circ}\text{C}$, designated IND

PIN ASSIGNMENT

| | | | |
|-----|----|----|-----------------|
| NC | 1 | 28 | V_{CC} |
| A12 | 2 | 27 | \overline{WE} |
| A7 | 3 | 26 | NC |
| A6 | 4 | 25 | A8 |
| A5 | 5 | 24 | A9 |
| A4 | 6 | 23 | A11 |
| A3 | 7 | 22 | \overline{OE} |
| A2 | 8 | 21 | A10 |
| A1 | 9 | 20 | \overline{CE} |
| A0 | 10 | 19 | DQ7 |
| DQ0 | 11 | 18 | DQ6 |
| DQ1 | 12 | 17 | DQ5 |
| DQ2 | 13 | 16 | DQ4 |
| GND | 14 | 15 | DQ3 |

28-Pin ENCAPSULATED PACKAGE
720-mil EXTENDED

PIN DESCRIPTION

| | |
|-----------------|--------------------|
| A0-A12 | - Address Inputs |
| DQ0-DQ7 | - Data In/Data Out |
| \overline{CE} | - Chip Enable |
| \overline{WE} | - Write Enable |
| \overline{OE} | - Output Enable |
| V_{CC} | - Power (+5V) |
| GND | - Ground |
| NC | - No Connect |

DESCRIPTION

The DS1225AB and DS1225AD are 65,536-bit, fully static, nonvolatile SRAMs organized as 8192 words by 8 bits. Each NV SRAM has a self-contained lithium energy source and control circuitry which constantly monitors V_{CC} for an out-of-tolerance condition. When such a condition occurs, the lithium energy source is automatically switched on and write protection is unconditionally enabled to prevent data corruption. The NV SRAMs can be used in place of existing 8k x 8 SRAMs directly conforming to the popular byte-wide 28-pin DIP standard. The devices also match the pinout of the 2764 EPROM and the 2864 EEPROM, allowing direct substitution while enhancing performance. There is no limit on the number of write cycles that can be executed and no additional support circuitry is required for microprocessor interfacing.

ABSOLUTE MAXIMUM RATINGS*

| | |
|---------------------------------------|--|
| Voltage on Any Pin Relative to Ground | -0.3V to +6.0V |
| Operating Temperature | 0°C to 70°C; -40°C to +85°C for IND parts |
| Storage Temperature | -40°C to +70°C; -40°C to +85°C for IND parts |
| Soldering Temperature | +260°C for 10 seconds |
| Caution: Do Not Reflow | (Wave or Hand Solder Only) |

* This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operation sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods of time may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS(T_A: See Note 10)

| PARAMETER | SYMBOL | MIN | TYP | MAX | UNITS | NOTES |
|-------------------------------|-----------------|------|-----|-----------------|-------|-------|
| DS1225AB Power Supply Voltage | V _{CC} | 4.75 | 5.0 | 5.25 | V | |
| DS1225AD Power Supply Voltage | V _{CC} | 4.50 | 5.0 | 5.5 | V | |
| Logic 1 | V _{IH} | 2.2 | | V _{CC} | V | |
| Logic 0 | V _{IL} | 0.0 | | +0.8 | V | |

(T_A: See Note 10)(V_{CC} = 5V ± 5% for DS1225AB)**DC ELECTRICAL CHARACTERISTICS**(V_{CC} = 5V ± 10% for DS1225AD)

| PARAMETER | SYMBOL | MIN | TYP | MAX | UNITS | NOTES |
|---|-------------------|------|------|------|-------|-------|
| Input Leakage Current | I _{IL} | -1.0 | | +1.0 | μA | |
| I/O Leakage Current CE > V _{IH} < V _{CC} | I _{IO} | -1.0 | | +1.0 | μA | |
| Output Current @ 2.4V | I _{OH} | -1.0 | | | mA | |
| Output Current @ 0.4V | I _{OL} | 2.0 | | | mA | |
| Standby Current CE = 2.2V | I _{CCS1} | | 5.0 | 10.0 | mA | |
| Standby Current CE = V _{CC} - 0.5V | I _{CCS2} | | 3.0 | 5.0 | mA | |
| Operating Current (Commercial) | I _{CC01} | | | 75 | mA | |
| Operating Current (Industrial) | I _{CC01} | | | 85 | mA | |
| Write Protection Voltage (DS1225AB) | V _{TP} | 4.50 | 4.62 | 4.75 | V | |
| Write Protection Voltage (DS1225AD) | V _{TP} | 4.25 | 4.37 | 4.5 | V | |

CAPACITANCE(T_A = 25°C)

| PARAMETER | SYMBOL | MIN | TYP | MAX | UNITS | NOTES |
|--------------------------|------------------|-----|-----|-----|-------|-------|
| Input Capacitance | C _{IN} | | 5 | 10 | pF | |
| Input/Output Capacitance | C _{I/O} | | 5 | 10 | pF | |

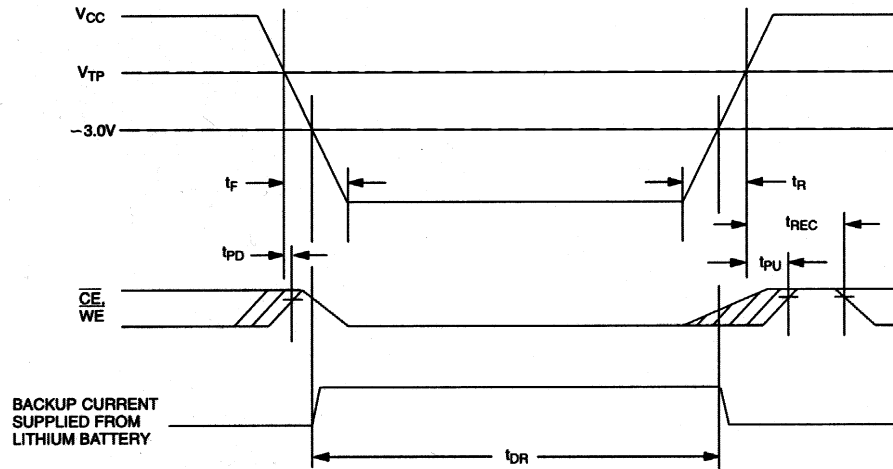
(T_A: See Note 10)(V_{CC} = 5V ± 5% for DS1225AB)(V_{CC} = 5V ± 10% for DS1225AD)**AC ELECTRICAL CHARACTERISTICS**

| PARAMETER | SYMBOL | DS1225AB-70 DS1225AD-70 | | DS1225AB-85 DS1225AD-85 | | UNITS | NOTES |
|---|------------------|----------------------------|-----|----------------------------|-----|-------|-------|
| | | MIN | MAX | MIN | MAX | | |
| Read Cycle Time | t _{RC} | 70 | | 85 | | ns | |
| Access Time | t _{ACC} | | 70 | | 85 | ns | |
| $\overline{\text{OE}}$ to Output Valid | t _{OE} | | 35 | | 45 | ns | |
| $\overline{\text{CE}}$ to Output Valid | t _{CO} | | 70 | | 85 | ns | |
| $\overline{\text{OE}}$ or $\overline{\text{CE}}$ to Output Active | t _{COE} | 5 | | 5 | | ns | 5 |
| Output High Z from Deselection | t _{OD} | | 25 | | 30 | ns | 5 |
| Output Hold from Address Change | t _{OH} | 5 | | 5 | | ns | |
| Write Cycle Time | t _{WC} | 70 | | 85 | | ns | |
| Write Pulse Width | t _{WP} | 55 | | 65 | | ns | 3 |
| Address Setup Time | t _{AW} | 0 | | 0 | | ns | |
| Write Recovery Time | t _{WR1} | 0 | | 0 | | ns | 12 |
| | t _{WR2} | 10 | | 10 | | ns | 13 |
| Output High Z from $\overline{\text{WE}}$ | t _{ODW} | | 25 | | 30 | ns | 5 |
| Output Active from $\overline{\text{WE}}$ | t _{OEW} | 5 | | 5 | | ns | 5 |
| Data Setup Time | t _{DS} | 30 | | 35 | | ns | 4 |
| Data Hold Time | t _{DH1} | 0 | | 0 | | ns | 12 |
| | t _{DH2} | 10 | | 10 | | ns | 13 |

AC ELECTRICAL CHARACTERISTICS (cont'd)

| PARAMETER | SYMBOL | DS1225AB- 150 DS1225AD- 150 | | DS1225AB-200 DS1225AD-200 | | UNITS | NOTES |
|---|-----------|--------------------------------|-----|------------------------------|-----|-------|-------|
| | | MIN | MAX | MIN | MAX | | |
| Read Cycle Time | t_{RC} | 150 | | 200 | | ns | |
| Access Time | t_{ACC} | | 150 | | 200 | ns | |
| \overline{OE} to Output Valid | t_{OE} | | 70 | | 100 | ns | |
| \overline{CE} to Output Valid | t_{CO} | | 150 | | 200 | ns | |
| \overline{OE} or \overline{CE} to Output Active | t_{COE} | 5 | | 5 | | ns | 5 |
| Output High Z from Deselection | t_{OD} | | 35 | | 35 | ns | 5 |
| Output Hold from Address Change | t_{OH} | 5 | | 5 | | ns | |
| Write Cycle Time | t_{WC} | 150 | | 200 | | ns | |
| Write Pulse Width | t_{WP} | 100 | | 100 | | ns | 3 |
| Address Setup Time | t_{AW} | 0 | | 0 | | ns | |
| Write Recovery Time | t_{WR1} | 0 | | 0 | | ns | 12 |
| | t_{WR2} | 10 | | 10 | | ns | 13 |
| Output High Z from \overline{WE} | t_{ODW} | | 35 | | 35 | ns | 5 |
| Output Active from \overline{WE} | t_{OEW} | 5 | | 5 | | ns | 5 |
| Data Setup Time | t_{DS} | 60 | | 80 | | ns | 4 |
| Data Hold Time | t_{DH1} | 0 | | 0 | | ns | 12 |
| | t_{DH2} | 10 | | 10 | | ns | 13 |

POWER-DOWN/POWER-UP CONDITION



SEE NOTE 11

POWER-DOWN/POWER-UP TIMING

 $(T_A : \text{See Note 10})$

| PARAMETER | SYMBOL | MIN | TYP | MAX | UNITS | NOTES |
|--|-----------|-----|-----|-----|---------|-------|
| V_{CC} Fail Detect to \overline{CE} and \overline{WE} Inactive | t_{PD} | | | 1.5 | μs | 11 |
| V_{CC} slew from V_{TP} to $0V$ | t_F | 300 | | | μs | |
| V_{CC} slew from $0V$ to V_{TP} | t_R | 300 | | | μs | |
| V_{CC} Valid to \overline{CE} and \overline{WE} Inactive | t_{PU} | | | 2 | ms | |
| V_{CC} Valid to End of Write Protection | t_{REC} | | | 125 | ms | |

 $(T_A = 25^\circ C)$

| PARAMETER | SYMBOL | MIN | TYP | MAX | UNITS | NOTES |
|------------------------------|----------|-----|-----|-----|-------|-------|
| Expected Data Retention Time | t_{DR} | 10 | | | years | 9 |

WARNING:

Under no circumstance are negative undershoots, of any amplitude, allowed when device is in battery backup mode.

NOTES:

1. \overline{WE} is high for a read cycle.
2. $\overline{OE} = V_{IH}$ or V_{IL} . If $\overline{OE} = V_{IH}$ during write cycle, the output buffers remain in a high-impedance state.
3. t_{WP} is specified as the logical AND of \overline{CE} and \overline{WE} . t_{WP} is measured from the latter of \overline{CE} or \overline{WE} going low to the earlier of \overline{CE} or \overline{WE} going high.
4. t_{DS} are measured from the earlier of \overline{CE} or \overline{WE} going high.
5. These parameters are sampled with a 5 pF load and are not 100% tested.
6. If the \overline{CE} low transition occurs simultaneously with or later than the \overline{WE} low transition, the output buffers remain in a high-impedance state during this period.
7. If the \overline{CE} high transition occurs prior to or simultaneously with the \overline{WE} high transition, the output buffers remain in a high-impedance state during this period.
8. If \overline{WE} is low or the \overline{WE} low transition occurs prior to or simultaneously with the \overline{CE} low transition, the output buffers remain in a high-impedance state during this period.
9. Each DS1225AB and each DS1225AD has a built-in switch that disconnects the lithium source until V_{CC} is first applied by the user. The expected t_{DR} is defined as accumulative time in the absence of V_{CC} starting from the time power is first applied by the user. This parameter is guaranteed by design and is not 100% tested.
10. All AC and DC electrical characteristics are valid over the full operating temperature range. For commercial products, this range is 0°C to 70°C. For industrial products (IND), this range is -40°C to +85°C.
11. In a power down condition the voltage on any pin may not exceed the voltage on V_{CC} .
12. t_{WR1} , t_{DH1} are measured from \overline{WE} going high.
13. t_{WR2} , t_{DH2} are measured from \overline{CE} going high.
14. DS1225 modules are recognized by Underwriters Laboratory (U.L.®) under file E99151.

DC TEST CONDITIONS

Outputs Open
 Cycle = 200ns for Operating Current
 All Voltages Are Referenced to Ground

AC TEST CONDITIONS

Output Load: 100 pF + 1TTL Gate
 Input Pulse Levels: 0 - 3.0V
 Timing Measurement Reference Levels
 Input: 1.5V
 Output: 1.5V
 Input Pulse Rise and Fall Times: 5ns

ORDERING INFORMATION

| PART NUMBER | TEMPERATURE RANGE | SUPPLY TOLERANCE | PIN/PACKAGE | SPEED GRADE |
|--------------------|--------------------------|-------------------------|--------------------|--------------------|
| DS1225AB-70 | 0°C to +70°C | 5V ± 5% | 28 / 720 EMOD | 70ns |
| DS1225AB-70+ | 0°C to +70°C | 5V ± 5% | 28 / 720 EMOD | 70ns |
| DS1225AB-70IND | -40°C to +85°C | 5V ± 5% | 28 / 720 EMOD | 70ns |
| DS1225AB-70IND+ | -40°C to +85°C | 5V ± 5% | 28 / 720 EMOD | 70ns |
| DS1225AB-85 | 0°C to +70°C | 5V ± 5% | 28 / 720 EMOD | 85ns |
| DS1225AB-85+ | 0°C to +70°C | 5V ± 5% | 28 / 720 EMOD | 85ns |
| DS1225AB-150 | 0°C to +70°C | 5V ± 5% | 28 / 720 EMOD | 150ns |
| DS1225AB-150+ | 0°C to +70°C | 5V ± 5% | 28 / 720 EMOD | 150ns |
| DS1225AB-150IND | -40°C to +85°C | 5V ± 5% | 28 / 720 EMOD | 150ns |
| DS1225AB-150IND+ | -40°C to +85°C | 5V ± 5% | 28 / 720 EMOD | 150ns |
| DS1225AB-200 | 0°C to +70°C | 5V ± 5% | 28 / 720 EMOD | 200ns |
| DS1225AB-200+ | 0°C to +70°C | 5V ± 5% | 28 / 720 EMOD | 200ns |
| DS1225AB-200IND | -40°C to +85°C | 5V ± 5% | 28 / 720 EMOD | 200ns |
| DS1225AB-200IND+ | -40°C to +85°C | 5V ± 5% | 28 / 720 EMOD | 200ns |
| DS1225AD-70 | 0°C to +70°C | 5V ± 10% | 28 / 720 EMOD | 70ns |
| DS1225AD-70+ | 0°C to +70°C | 5V ± 10% | 28 / 720 EMOD | 70ns |
| DS1225AD-70IND | -40°C to +85°C | 5V ± 10% | 28 / 720 EMOD | 70ns |
| DS1225AD-70IND+ | -40°C to +85°C | 5V ± 10% | 28 / 720 EMOD | 70ns |
| DS1225AD-85 | 0°C to +70°C | 5V ± 10% | 28 / 720 EMOD | 85ns |
| DS1225AD-85+ | 0°C to +70°C | 5V ± 10% | 28 / 720 EMOD | 85ns |
| DS1225AD-150 | 0°C to +70°C | 5V ± 10% | 28 / 720 EMOD | 150ns |
| DS1225AD-150+ | 0°C to +70°C | 5V ± 10% | 28 / 720 EMOD | 150ns |
| DS1225AD-150IND | -40°C to +85°C | 5V ± 10% | 28 / 720 EMOD | 150ns |
| DS1225AD-150IND+ | -40°C to +85°C | 5V ± 10% | 28 / 720 EMOD | 150ns |
| DS1225AD-200 | 0°C to +70°C | 5V ± 10% | 28 / 720 EMOD | 200ns |
| DS1225AD-200+ | 0°C to +70°C | 5V ± 10% | 28 / 720 EMOD | 200ns |
| DS1225AD-200IND | -40°C to +85°C | 5V ± 10% | 28 / 720 EMOD | 200ns |
| DS1225AD-200IND+ | -40°C to +85°C | 5V ± 10% | 28 / 720 EMOD | 200ns |

+ Denotes lead-free/RoHS-compliant product.